Advanced Materials and Device Concepts for Semiconductor Lasers in the Near- to Far-Infrared

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In this talk our present progress on edge emitters based on GaSb substrate as well as InP based Quantum Cascade Lasers (QCLs), novel type-II InP-based long-wavelength lasers and Vertical Cavity Surface Emitting devices (VCSELs) will be presented. The short-cavity VCSELs are defining new standards for high-speed, high-power and wide tunability, the edge emitters with adjusted active regions extend wavelengths beyond 3.5 μm whereas the QCLs offer wavelength shifts in both directions, near- and far-infrared.

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